Octal Bus Buffer

The MC74LVX541 is an advanced high speed CMOS octal bus buffer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The MC74LVX541 is a noninverting type. When either $\overline{OE1}$ or $\overline{OE2}$ are high, the terminal outputs are in the high impedance state.

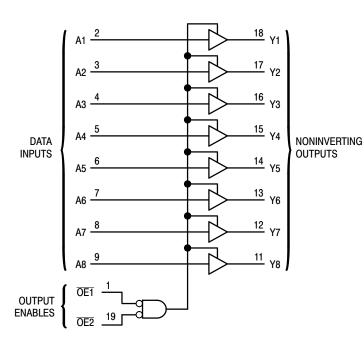
The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7.0 V, allowing the interface of 5.0 V systems to 3.0 V systems.

Features

- High Speed: $t_{PD} = 5.0$ ns (Typ) at $V_{CC} = 3.3$ V
- Low Power Dissipation: $I_{CC} = 4 \mu A$ (Max) at $T_A = 25^{\circ}C$
- High Noise Immunity: $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2 V to 3.6 V Operating Range
- Low Noise: $V_{OLP} = 1.2 V (Max)$
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- Chip Complexity: 134 FETs or 33.5 Equivalent Gates
- ESD Performance:

Human Body Model > 2000 V; Machine Model > 200 V

• These Devices are Pb-Free and are RoHS Compliant







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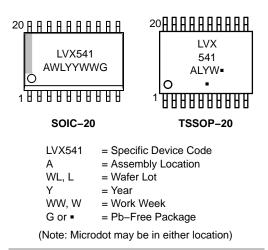
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PIN ASSIGNMENT

OE1	1●	20	□ v _{cc}
A1 [2	19	
A2 [3	18] Y1
A3 [4	17] Y2
A4 [5	16] Y3
A5 [6	15] Y4
A6 [7	14] Y5
A7 [8	13] Y6
A8 [9	12] Y7
GND [10	11] Y8

MARKING DIAGRAMS



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

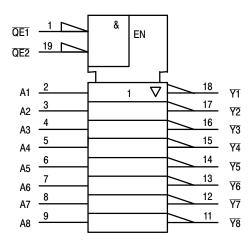


Figure 2. IEC Logic Diagram

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V _{CC}	DC Supply Voltage		- 0.5 to + 7.0	V
V _{in}	DC Input Voltage		- 0.5 to + 7.0	V
V _{out}	DC Output Voltage		-0.5 to V _{CC} + 0.5	V
I _{IK}	Input Diode Current		- 20	mA
I _{OK}	Output Diode Current		± 20	mA
l _{out}	DC Output Current, per Pin		± 25	mA
I _{CC}	DC Supply Current, V _{CC} and G	ND Pins	± 50	mA
P _D	Power Dissipation in Still Air, SOIC Packages† TSSOP Package†		500 450	mW
T _{stg}	Storage Temperature		– 65 to + 150	°C

FUNCTION TABLE

Inputs	Output V	
OE2	A	Output Y
L	L	L
L	Н	Н
Х	Х	Z
н	Х	Z
	OE2 L L X	L L L H X X

This device contains protection
circuitry to guard against damage
due to high static voltages or electric
fields. However, precautions must
be taken to avoid applications of any
voltage higher than maximum rated
voltages to this high-impedance cir-
cuit. For proper operation, V _{in} and
Vout should be constrained to the
range GND \leq (V _{in} or V _{out}) \leq V _{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating: SOIC Package: -7 mW/°C from 65° to 125°C

TSSOP Package: -6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage	2.0	3.6	V
V _{in}	DC Input Voltage	0	5.5	V
V _{out}	DC Output Voltage	0	V _{CC}	V
T _A	Operating Temperature, All Package Types	-40	+85	°C
t _r , t _f	Input Rise and Fall Time V_{CC} = 3.3 V ± 0.3 V	0	100	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

			Vec	V_{CC} $T_A = 25^{\circ}C$		С	$T_A = -40$) to 85°C	
Symbol	Parameter	Test Conditions	V	Min	Тур	Max	Min	Max	Unit
V _{IH}	Minimum High-Level Input Voltage		2.0 3.0 3.6	1.50 2.0 2.4			1.50 2.0 2.4		V
V _{IL}	Maximum Low-Level Input Voltage		2.0 3.0 3.6			0.50 0.80 0.80		0.50 0.80 0.80	V
V _{OH}	Minimum High-Level Output Voltage $V_{in} = V_{IH} \text{ or } V_{IL}$	$I_{OH} = -50 \ \mu A$ $I_{OH} = -50 \ \mu A$ $I_{OH} = -4 \ m A$	2.0 3.0 3.0	1.9 2.9 2.58	2.0 3.0		1.9 2.9 2.48		V
V _{OL}	Maximum Low–Level Output Voltage $V_{in} = V_{IH}$ or V_{IL}	$I_{OL} = 50 \ \mu A$ $I_{OL} = 50 \ \mu A$ $I_{OL} = 4 \ m A$	2.0 3.0 3.0		0.0 0.0	0.1 0.1 0.36		0.1 0.1 0.44	V
I _{in}	Maximum Input Leakage Current	V _{in} = 5.5 V or GND	0 to 3.6			±0.1		±1.0	μΑ
I _{OZ}	Maximum Three-State Leakage Current	$V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or } GND$	3.6			±0.2 5		±2.5	μΑ
I _{CC}	Maximum Quiescent Supply Current	$V_{in} = V_{CC} \text{ or } GND$	3.6			4.0		40.0	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS (Input t_r = t_f = 3.0 ns)

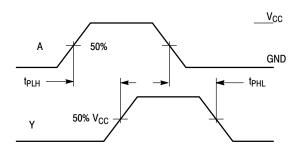
				Т	T _A = 25°C		$T_{A} = -40$) to 85°C	Unit
Symbol	Parameter	Test Conditions		Min	Тур	Max	Min	Max	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, A to Y	V _{CC} = 2.7 V	C _L = 15 pF C _L = 50 pF		5.0 7.5	7.0 10.5	1.0 1.0	8.5 12.0	ns
		$V_{CC} = 3.3 \pm 0.3 V$	C _L = 15 pF C _L = 50 pF		3.5 5.0	5.0 7.0	1.0 1.0	6.0 8.0	
t _{PZL} , t _{PZH}	Output Enable Time, OE to Y	$V_{CC} = 2.7 V$ $R_L = 1 k\Omega$	C _L = 15 pF C _L = 50 pF		6.8 9.3	10.5 14.0	1.0 1.0	12.5 16.0	ns
		V_{CC} = 3.3 ± 0.3 V R _L = 1 k Ω	C _L = 15 pF C _L = 50 pF		4.7 6.2	7.2 9.2	1.0 1.0	8.5 10.5	
t _{PLZ} , t _{PHZ}	Output Disable Time, OE to Y	$V_{CC} = 2.7 V$ $R_L = 1 k\Omega$	C _L = 50 pF		11.2	15.4	1.0	17.5	ns
		$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $R_{L} = 1 \text{ k}\Omega$	C _L = 50 pF		6.0	8.8	1.0	10.0	
t _{OSLH} , t _{OSHL}	Output to Output Skew	V _{CC} = 2.7 V (Note 1)	C _L = 50 pF			1.5		1.5	ns
		$V_{CC} = 3.3 \pm 0.3 V$ (Note 1)	C _L = 50 pF			1.0		1.0	ns
C _{in}	Maximum Input Capacitance				4.0	10		10	pF
C _{out}	Maximum Three–State Output Capacitance (Output in High Impedance State)				6.0				pF
				Typical @ 25°C, V _{CC} = 5.0 V			0 V		
C _{PD}	Power Dissipation Capacitance (Note 2)					18	3		pF

Parameter guaranteed by design. t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|.
C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC} / 8 (per bit). C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}, C_L = 50 \text{ pF}, V_{CC} = 3.3 \text{ V}$)

		T _A = 25°C		
Symbol	Parameter		Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.5	0.8	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}		-0.8	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		2.0	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		0.8	V

SWITCHING WAVEFORMS



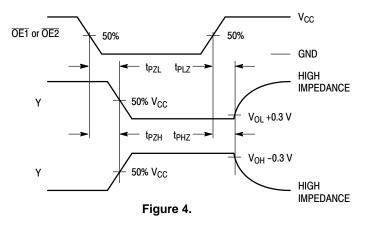
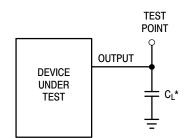


Figure 3.

TEST CIRCUITS



*Includes all probe and jig capacitance

*Includes all probe and jig capacitance Figure 5.



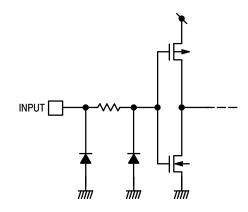


Figure 7. Input Equivalent Circuit

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74LVX541DWG	SOIC-20 (Pb-Free)	38 Units / Rail
MC74LVX541DTR2G	TSSOP-20 (Pb-Free)	2500 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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